



INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁷ : G01N 27/24	A2	(11) International Publication Number: WO 00/46593 (43) International Publication Date: 10 August 2000 (10.08.00)
---	----	---

(21) International Application Number: PCT/US00/03308

(22) International Filing Date: 8 February 2000 (08.02.00)

(30) Priority Data:
60/119,166 8 February 1999 (08.02.99) US

(71) Applicant: ANALATOM INCORPORATED [US/US]; Suite 9, 540 Weddell Drive, Sunnyvale, CA 94089 (US).

(72) Inventor: WILSON, Alan; 26 Nerissa Street, Burwood, VIC 3125 (AU).

(74) Agent: PERRY, Clifford, B.; Heller Ehrman White & McAuliffe, Suite 700, 4250 Executive Square, La Jolla, CA 92037 (US).

(81) Designated States: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published*Without international search report and to be republished upon receipt of that report.*

(54) Title: A MICRO-ELECTRONIC BOND DEGRADATION SENSOR AND METHOD OF MANUFACTURE

(57) Abstract

A micro-electronic bond degradation sensor includes a sensor substrate having sensor circuitry and a sensor stud and a power stud extending therefrom. The sensor circuitry includes a voltage-to-current amplifier having an input coupled to sensor stud and an output coupled to the power stud. The voltage-to-current amplifier is operable to convert a voltage signal occurring along the sensor stud to a current signal output along the power stud.

